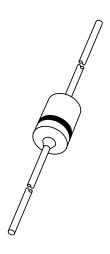
## **DISCRETE SEMICONDUCTORS**

## DATA SHEET



# **BZX79 series**Voltage regulator diodes

Product data sheet Supersedes data of 1999 May 25 2002 Feb 27



## Voltage regulator diodes

#### **BZX79** series

#### **FEATURES**

- Total power dissipation: max. 500 mW
- Two tolerance series: ±2%, and approx. ±5%
- Working voltage range: nom. 2.4 to 75 V (E24 range)
- Non-repetitive peak reverse power dissipation: max. 40 W.

#### **APPLICATIONS**

· Low voltage stabilizers or voltage references.

#### DESCRIPTION

Low-power voltage regulator diodes in hermetically sealed leaded glass SOD27 (DO-35) packages. The diodes are available in the normalized E24  $\pm 2\%$  (BZX79-B) and approx.  $\pm 5\%$  (BZX79-C) tolerance range. The series consists of 37 types with nominal working voltages from 2.4 to 75 V.

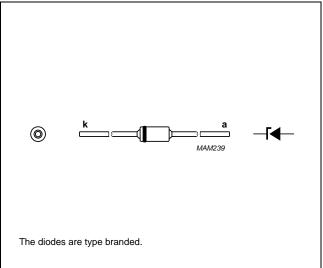


Fig.1 Simplified outline (SOD27; DO-35) and symbol.

#### **LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I <sub>F</sub>	continuous forward current		_	250	mA
I <sub>ZSM</sub>	non-repetitive peak reverse current	$t_p$ = 100 μs; square wave; $T_j$ = 25 °C prior to surge	see Tables 1 and 2		A
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 50 °C; note 1	_	400	mW
		T <sub>amb</sub> = 50 °C; note 2	_	500	mW
P <sub>ZSM</sub>	non-repetitive peak reverse power dissipation	$t_p$ = 100 μs; square wave; $T_j$ = 25 °C prior to surge; see Fig.3	_	40	W
T <sub>stg</sub>	storage temperature		-65	+200	°C
Tj	junction temperature		-65	+200	°C

#### Notes

- 1. Device mounted on a printed circuit-board without metallization pad; lead length max.
- 2. Tie-point temperature  $\leq$  50 °C; max. lead length 8 mm.

#### **ELECTRICAL CHARACTERISTICS**

#### Total BZX79-B and BZX79-C series

T<sub>j</sub> = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MAX.	UNIT
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 10 mA; see Fig.4	0.9	V

## Voltage regulator diodes

## BZX79 series

SYMBOL	PARAMETER	CONDITIONS	MAX.	UNIT
I <sub>R</sub>	reverse current			
	BZX79-B/C2V4	V <sub>R</sub> = 1 V	50	μΑ
	BZX79-B/C2V7	V <sub>R</sub> = 1 V	20	μΑ
	BZX79-B/C3V0	V <sub>R</sub> = 1 V	10	μΑ
	BZX79-B/C3V3	V <sub>R</sub> = 1 V	5	μΑ
	BZX79-B/C3V6	V <sub>R</sub> = 1 V	5	μΑ
	BZX79-B/C3V9	V <sub>R</sub> = 1 V	3	μΑ
	BZX79-B/C4V3	V <sub>R</sub> = 1 V	3	μΑ
	BZX79-B/C4V7	V <sub>R</sub> = 2 V	3	μΑ
	BZX79-B/C5V1	V <sub>R</sub> = 2 V	2	μΑ
	BZX79-B/C5V6	V <sub>R</sub> = 2 V	1	μΑ
	BZX79-B/C6V2	V <sub>R</sub> = 4 V	3	μΑ
	BZX79-B/C6V8	$V_R = 4 V$	2	μΑ
	BZX79-B/C7V5	V <sub>R</sub> = 5 V	1	μΑ
	BZX79-B/C8V2	$V_R = 5 V$	700	nA
	BZX79-B/C9V1	V <sub>R</sub> = 6 V	500	nA
	BZX79-B/C10	V <sub>R</sub> = 7 V	200	nA
	BZX79-B/C11	V <sub>R</sub> = 8 V	100	nA
	BZX79-B/C12	V <sub>R</sub> = 8 V	100	nA
	BZX79-B/C13	V <sub>R</sub> = 8 V	100	nA
	BZX79-B/C15 to BZX79-B/C75	$V_R = 0.7V_{Znom}$	50	nA

## Voltage regulator diodes

### BZX79 series

**NON-REPETITIVE PEAK** at  $t_p = 100 \mu s$ ;  $T_{amb} = 25$ REVERSE CURRENT I<sub>SSM</sub> (A) MAX. 6.0 0.9 0.9 0.9 0.9 0.9 6.0 4.0 4.0 3.0 3.0 2.0 5. 1.5 DIODECAP. at f = 1 MHz;  $V_R = 0 V$ C<sub>d</sub> (pF) 450 450 300 300 300 200 200 150 450 450 450 150 150 90 85 85 80 70 9 9 55 13.0 14.0 18.0 20.0 22.0 10.0 11.0 16.0 (see Figs 5 and 6) 2.5 4.5 5.3 8.0 9.0 0.2 1.2 7.0 6.2 at  $I_{Ztest} = 5 \text{ mA}$ 3.7 TEMP. COEFF. 0 0 0 0  $S_z$  (mV/K) Ę. -2.0-2.4-2.5-2.5 <u>1.</u> -0.8 12.4 15.6 17.6 19.6 -2.41.4 14.4 -2.1 1.2 2.3 3.0 4.0 4.6 5.5 6.4 7.4 9.4 8.4 Ζ̈́ -3.5 -3.5-3.5 -3.5 -3.5 -3.5 -3.5 -2.0 12.3 -2.710.4 12.4 14.1 2.5 3.2 4.5 0.4 1.2 3.8 5.4 0.9 7.0 9.2 5. at  $I_{Ztest} = 5 \text{ mA}$ **DIFFERENTIAL RESISTANCE** 100 100 40 20 20 25 45 92 10 15 15 5 15 40 55 55 90 90 90 9 30 30 F. 15 10 15 20 75 80 85 85 85 80 40 10 10 10 10 10 9 9 9 9 9 ω Iztest = 1 mA MAX. 009 9 9 009 900 480 200 225 225 009 009 500 400 100 150 150 170 200 150 150 250 80 80 80 TYP. 275 300 325 375 410 400 350 400 425 80 40 30 8 4 40 50 50 50 50 50 09 9 MAX. Tol. approx. 10.6 11.6 15.6 21.2 23.3 25.6 12.7 14.1 17.1 19.1 4.6 9.6 3.5 3.8 4. 5.0 5.4 6.0 9.9 8.7 *NORKING VOLTAGE* at Iztest = 5 mA Ζ̈́ 13.8 16.8 18.8 20.8 22.8 10.4 12.4 15.3 2.5 8.5 2.2 2.8 3.4 4.0 4.4 4.8 5.2 5.8 6.4 7.0 9.4 3.1 3.7 7.7 22.40 MAX. 12.20 15.30 20.40 24.50 10.20 11.20 13.30 16.30 18.40 Tol. ±2% (B) 8.36 9.28 2.45 2.75 3.06 3.98 4.39 4.79 5.20 6.32 6.94 7.65 3.37 3.67 5.71 10.80 15.70 19.60 21.60 11.80 14.70 17.60 12.70 50 2.35 2.65 3.23 3.53 5.49 6.08 99.9 7.35 8.04 8.92 9.80 2.94 3.82 5.00 4.21 4.61 23. CXX 3\3 3//6 3/\9 4\3 5/16 6/8 7\\5 6V2 8V2 477 5V1 9V1 10 3 5 16

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Fable 1 Per type, BZX79-B/C2V4 to BZX79-B/C24

= 25 °C unless otherwise specified

## Voltage regulator diodes

BZX79 series

**NON-REPETITIVE PEAK** at  $t_p = 100 \mu s$ ;  $T_{amb} = 25$ REVERSE CURRENT I<sub>SSM</sub> (A) MAX. 9.0 0.4 0.7 DIODECAP. at f = 1 MHz;  $V_R = 0 V$ C<sub>d</sub> (pF) 45 45 20 4 4 35 50 4 40 35 25.3 29.4 33.4 37.4 41.2 46.6 51.8 57.2 63.8 71.6 79.8 88.6 (see Figs 5 and 6) at  $I_{Ztest} = 2 mA$ TEMP. COEFF.  $S_z$  (mV/K) TP. 28.7 31.8 34.8 38.8 42.9 46.9 52.0 64.4 80.2 25.7 71.7 22.7 Ż 18.0 20.6 23.3 38.6 58.8 9.59 26.0 31.4 35.0 42.2 73.4 28.7 at  $I_{Ztest} = 2 mA$ MAX. DIFFERENTIAL RESISTANCE 215 255 170 180 200 240 130 150 80 80 90 80 ₹ . 25 30 35 40 45 20 09 20 80 90 at  $I_{Ztest} = 0.5 \text{ mA}$ MAX. 300 300 325 350 350 375 375 400 425 450 475 500 TYP. 100 120 170 150 20 75 80 80 9 82 85 90 MAX. Tol. approx. 28.9 32.0 35.0 38.0 41.0 46.0 50.0 54.0 0.09 0.99 72.0 79.0 ±5% (C) **WORKING VOLTAGE** at  $I_{Ztest} = 2 mA$ Ζ̈́ 52.0 28.0 31.0 34.0 37.0 40.0 44.0 48.0 58.0 64.0 70.0 25.1 MAX. 57.10 63.20 30.60 33.70 36.70 43.90 47.90 69.40 76.50 27.50 39.80 52.00 Tol. ±2% (B) 32.30 29.40 42.10 46.10 54.90 60.80 26.50 35.30 38.20 50.00 09.99 73.50 CXX Вххх 43 36 39 47 26 62 68 51

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Table 2 Per type, BZX79-B/C27 to BZX79-B/C75

= 25 °C unless otherwise specified.

## Voltage regulator diodes

BZX79 series

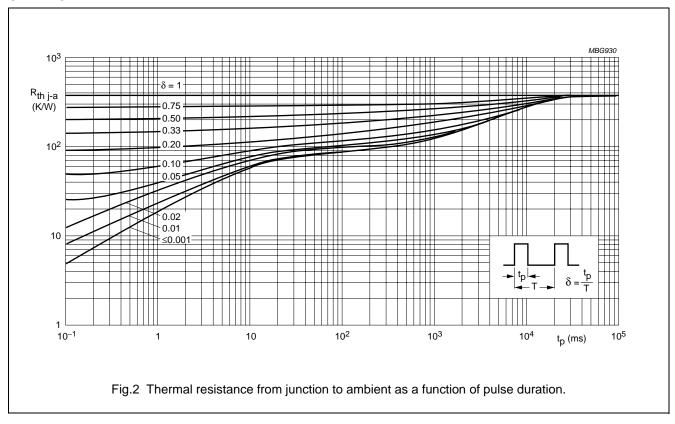
#### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R <sub>th j-tp</sub>	thermal resistance from junction to tie-point	lead length 8 mm.	300	K/W
R <sub>th j-a</sub>	thermal resistance from junction to ambient	lead length max.; see Fig.2 and note 1	380	K/W

#### Note

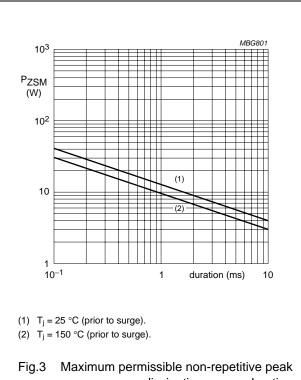
1. Device mounted on a printed circuit-board without metallization pad.

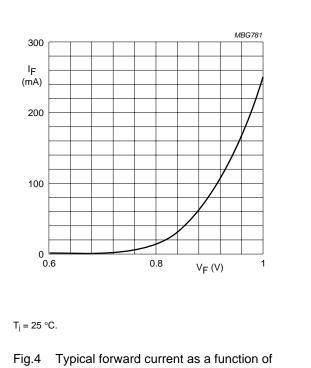
#### **GRAPHICAL DATA**



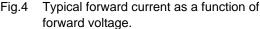
## Voltage regulator diodes

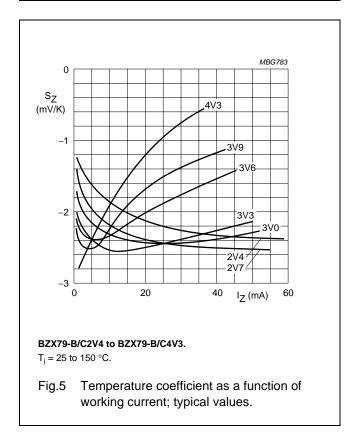
#### BZX79 series

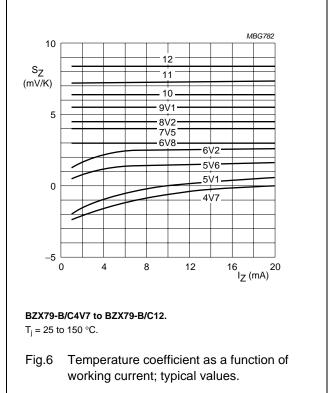




reverse power dissipation versus duration.







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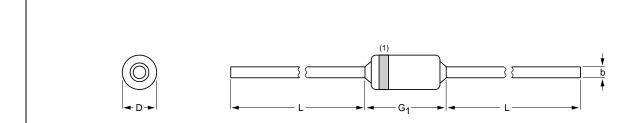
## Voltage regulator diodes

## BZX79 series

#### **PACKAGE OUTLINE**

Hermetically sealed glass package; axial leaded; 2 leads

SOD27



#### **DIMENSIONS** (mm are the original dimensions)

UNIT	b max.	D max.	G <sub>1</sub> max.	L min.
mm	0.56	1.85	4.25	25.4

0 1 2 mm scale

#### Note

1. The marking band indicates the cathode.

OUTLINE		REFER	ENCES	EUROPEAN	
VERSION	IEC	JEDEC	EIAJ	PROJECTION	ISSUE DATE
SOD27	A24	DO-35	SC-40		97-06-09

## Voltage regulator diodes

BZX79 series

#### **DATA SHEET STATUS**

DOCUMENT STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)</sup>	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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Printed in The Netherlands 613514/03/pp10 Date of release: 2002 Feb 27 Document order number: 9397 750 09387

